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October 2016

# FFSH30120ADN\_F155

# Silicon Carbide Schottky Diode 1200 V, 30 A

#### **Features**

- Max Junction Temperature 175 °C
- · Avalanche Rated 145 mJ
- · High Surge Current Capacity
- · Positive Temperature Coefficient
- · Ease of Paralleling
- · No Reverse Recovery / No Forward Recovery

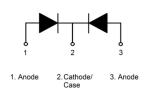
### **Applications**

- · General Purpose
- · SMPS, Solar Inverter, UPS
- · Power Switching Circuits

## **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.





#### **Absolute Maximum Ratings** T<sub>C</sub> = 25 °C unless otherwise noted. (per leg)

Symbol	Parameter		FFSH30120ADN_F155	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		1200	V
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 1)	145	mJ
I <sub>F</sub>	Continuous Rectified Forward Current @ T	c < 148 °C	15* / 30**	Α
	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25 °C, 10 μs	1030	Α
IF, Max		T <sub>C</sub> = 150 °C, 10 μs	990	Α
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	125	Α
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	50	Α
Ptot	Dower Dissination	T <sub>C</sub> = 25 °C	195	W
Fioi	Power Dissipation	T <sub>C</sub> = 150 °C	32	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range TO247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

#### **Thermal Characteristic**

Symbol	Parameter	FFSH30120ADN_F155	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.77* / 0.32**	°C/W

<sup>\*</sup> Per leg, \*\* Per Device

#### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity	
FFSH30120ADN_F155	FFSH30120ADN	TO-247 Long Lead	Tube	N/A	N/A	30 units	

# **Electrical Characteristics** T<sub>C</sub> = 25 °C unless otherwise noted. (per leg)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
		I <sub>F</sub> = 15 A, T <sub>C</sub> = 25 °C	-	1.45	1.75	
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 15 A, T <sub>C</sub> = 125 °C	-	1.7	2	V
		I <sub>F</sub> = 15 A, T <sub>C</sub> = 175 °C	-	2	2.4	
	Reverse Current	$V_R = 1200 \text{ V}, T_C = 25  ^{\circ}\text{C}$	-	-	200	μА
I <sub>R</sub>		$V_R = 1200 \text{ V}, T_C = 125  ^{\circ}\text{C}$	-	-	300	
		$V_R = 1200 \text{ V}, T_C = 175  ^{\circ}\text{C}$	-	-	400	
$Q_C$	Total Capacitive Charge	V = 800 V	-	95	-	nC
С		$V_R = 1 \text{ V, } f = 100 \text{ kHz}$	-	936	-	
	Total Capacitance	$V_R = 400 \text{ V}, f = 100 \text{ kHz}$	-	86	-	pF
		$V_R = 800 \text{ V}, f = 100 \text{ kHz}$	-	68	-	

# Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted (per leg).

Figure 1. Forward Characteristics

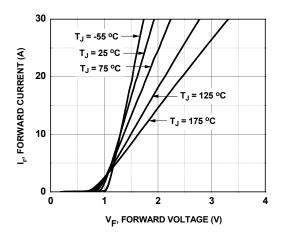


Figure 3. Reverse Characteristics

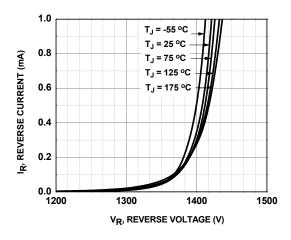


Figure 2. Reverse Characteristics

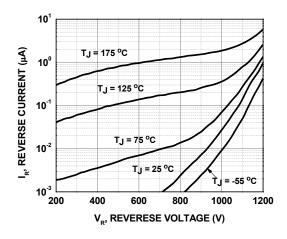
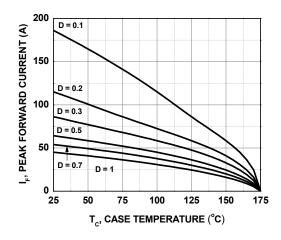


Figure 4. Current Derating



Notes: 1: EAS of 145 mJ is based on starting  $T_J$  = 25 °C, L = 0.5 mH,  $I_{AS}$  = 24 A, V = 150 V.

# **Typical Characteristics** $T_J = 25$ °C unless otherwise noted (per leg, continue).

Figure 5. Power Derating

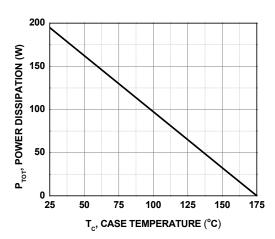


Figure 7. Capacitance vs. Reverse Voltage

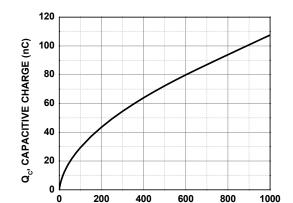
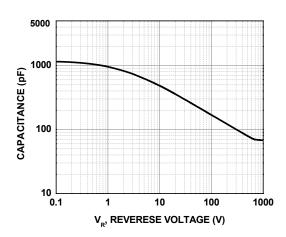


Figure 6. Capacitive Charge vs.

Reverse Voltage

Figure 8. Capacitance Stored Energy

V<sub>B</sub>, REVERSE VOLTAGE (V)



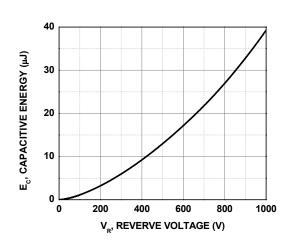
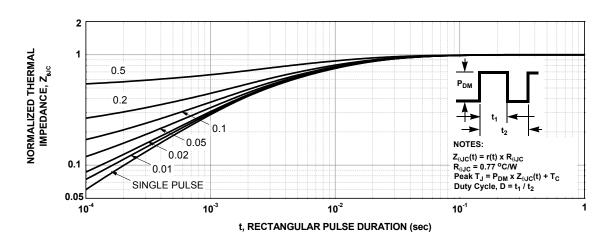
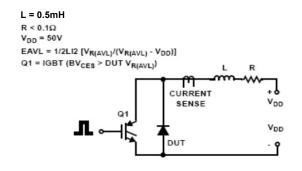


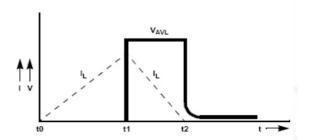
Figure 9. Junction-to-Case Transient Thermal Response Curve

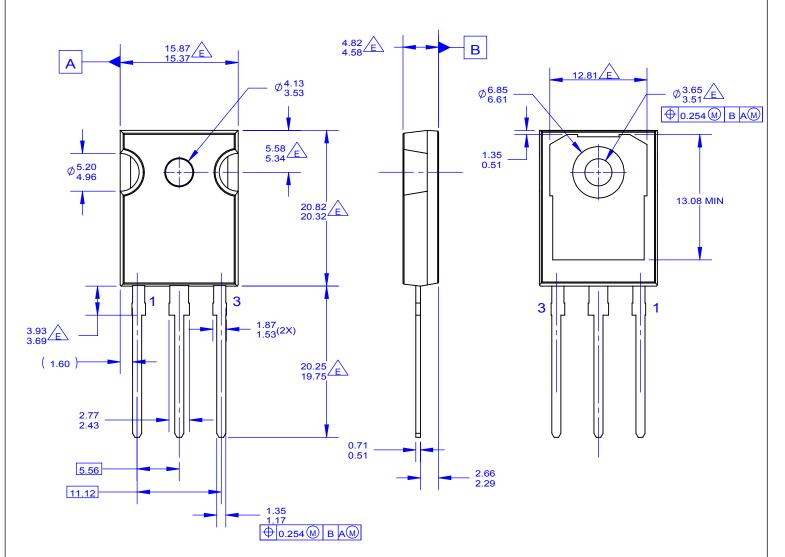


# **Test Circuit and Waveforms**

Figure 10. Unclamped Inductive Switching Test Circuit & Waveform







#### NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994





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